



# 2N7002E

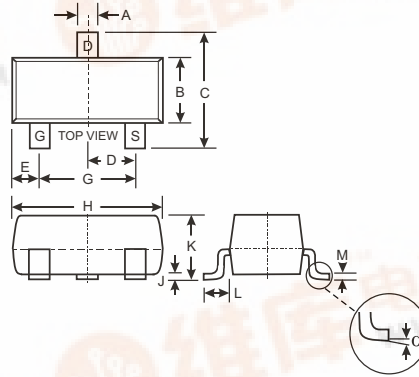
## N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

### Features

- Low On-Resistance:  $R_{DS(ON)}$
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Lead Free/RoHS Compliant (Note 2)

### Mechanical Data

- Case: SOT-23
- Case Material: UL Flammability Classification Rating 94V-0
- Moisture sensitivity: Level 1 per J-STD-020C
- Terminals: Solderable per MIL-STD-202, Method 208
- Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe).
- Terminal Connections: See Diagram
- Marking (See Page 2): K7B
- Ordering & Date Code Information: See Page 2
- Weight: 0.008 grams (approx.)



SOT-23		
Dim	Min	Max
A	0.37	0.51
B	1.20	1.40
C	2.30	2.50
D	0.89	1.03
E	0.45	0.60
G	1.78	2.05
H	2.80	3.00
J	0.013	0.10
K	0.903	1.10
L	0.45	0.61
M	0.085	0.180
	0	8
All Dimensions in mm		

### Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Value	Units
Drain-Source Voltage	$V_{DSS}$	60	V
Drain-Gate Voltage $R_{GS} = 1.0M$	$V_{DGR}$	60	V
Gate-Source Voltage	$V_{GSS}$	$\pm 20$ $\pm 40$	V
Drain Current	$I_D$	240	mA
Total Power Dissipation (Note 1)	$P_d$	300	mW
Thermal Resistance, Junction to Ambient	$R_{JA}$	417	$^\circ\text{C}/\text{W}$
Operating and Storage Temperature Range	$T_j, T_{STG}$	-55 to +150	$^\circ\text{C}$

- Note: 1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at <http://www.diodes.com/datasheets/ap02001.pdf>.  
2. No purposefully added lead.

## Electrical Characteristics @ T<sub>A</sub> = 25 °C unless otherwise specified

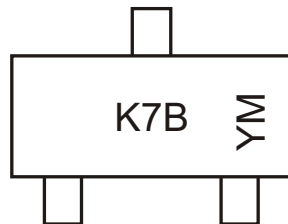
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 3)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	60	70		V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 10 A
Zero Gate Voltage Drain Current	I <sub>DSS</sub>			1.0 500	μA	V <sub>DS</sub> = 60V, V <sub>GS</sub> = 0V @ T <sub>C</sub> = 25°C @ T <sub>C</sub> = 125°C
Gate-Body Leakage	I <sub>GSS</sub>			±10	nA	V <sub>GS</sub> = ±15V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 3)</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	1.0		2.5	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 A
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>		1.6 2.0	3 4		V <sub>GS</sub> = 10V, I <sub>D</sub> = 250mA V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 200mA @ T <sub>J</sub> = 25°C
On-State Drain Current	I <sub>D(ON)</sub>	0.8	1.0		A	V <sub>GS</sub> = 10V, V <sub>DS</sub> = 7.5V
Forward Transconductance	g <sub>FS</sub>	80			mS	V <sub>DS</sub> = 10V, I <sub>D</sub> = 0.2A
<b>DYNAMIC CHARACTERISTICS</b>						
Input Capacitance	C <sub>iss</sub>		22	50	pF	V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V f = 1.0MHz
Output Capacitance	C <sub>oss</sub>		11	25	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>		2.0	5.0	pF	
<b>SWITCHING CHARACTERISTICS</b>						
Turn-On Delay Time	t <sub>D(ON)</sub>		7.0	20	ns	V <sub>DD</sub> = 30V, I <sub>D</sub> = 0.2A, R <sub>L</sub> = 150 Ω, V <sub>GEN</sub> = 10V, R <sub>GEN</sub> = 25 Ω
Turn-Off Delay Time	t <sub>D(OFF)</sub>		11	20	ns	

## Ordering Information (Note 4)

Device	Packaging	Shipping
2N7002E-7-F	SOT-23	3000/Tape & Reel

- Notes:
3. Short duration test pulse used to minimize self-heating effect.
  4. For Packaging Details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

## Marking Information



K7B = Product Type Marking Code  
 YM = Date Code Marking  
 Y = Year ex: P = 2003  
 M = Month ex: 9 = September

Date Code Key

Year	2003	2004	2005	2006	2007	2008	2009
Code	P	R	S	T	U	V	W

Month	Jan	Feb	March	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

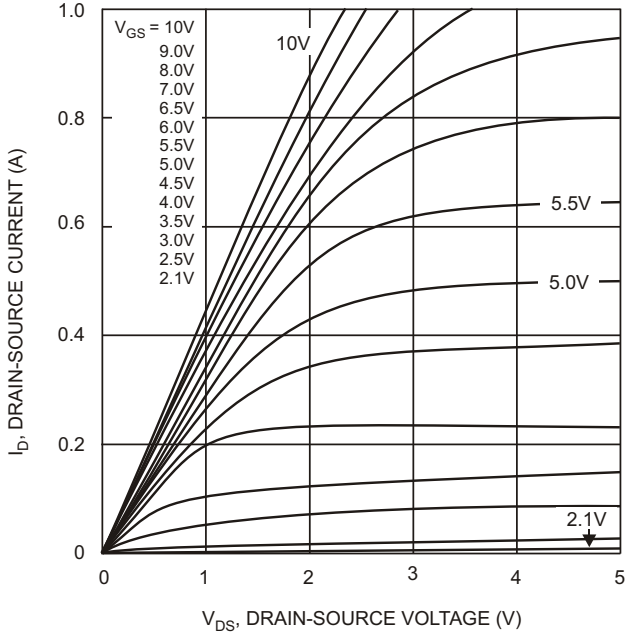


Fig. 1 On-Region Characteristics

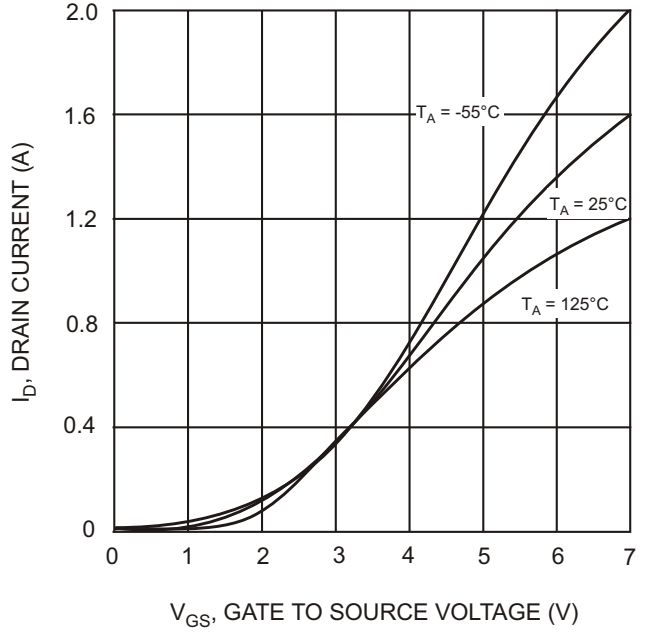


Fig. 2 Drain Current vs. Gate-Source Voltage

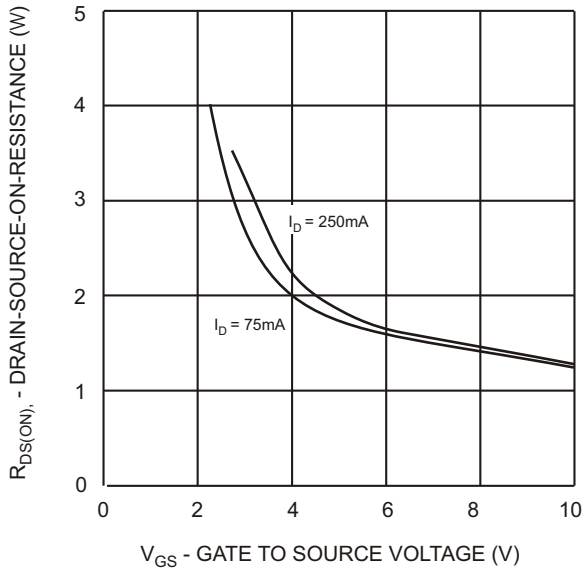


Fig. 3 On Resistance vs. Gate to Source Voltage

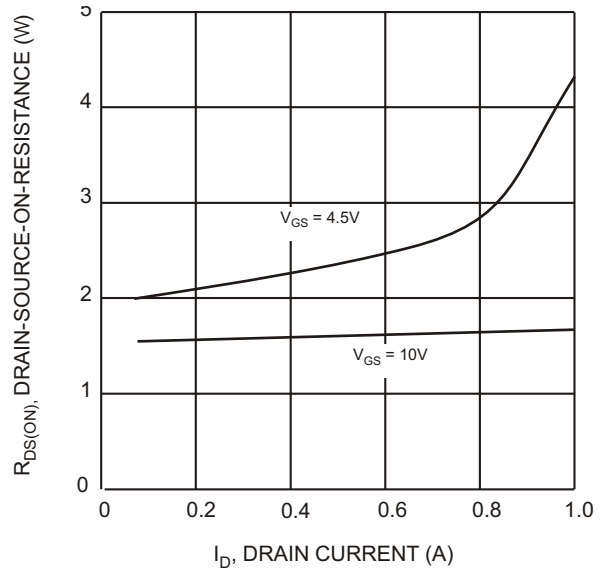


Fig. 4 On Resistance vs. Drain Current

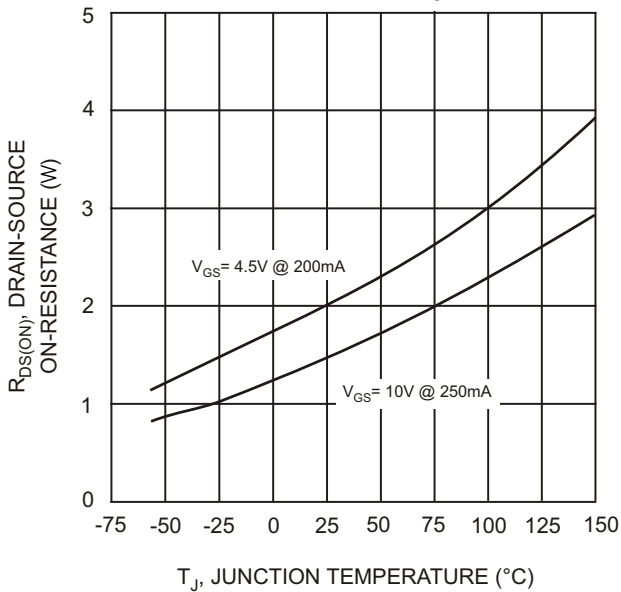


Fig. 5 On-Resistance vs. Junction Temperature

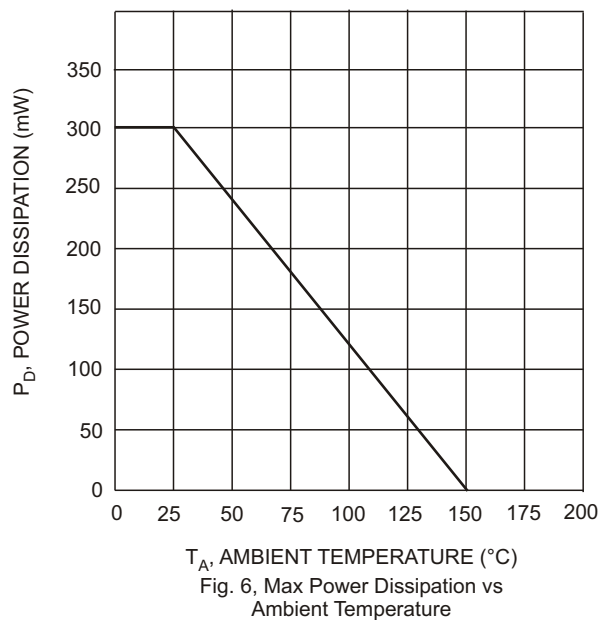


Fig. 6 Max Power Dissipation vs Ambient Temperature



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